



January, 2006

FPAB30PH60

## FPAB30PH60

### Smart Power Module for Front-End Rectifier

#### General Description

FPAB30PH60 is an advanced smart power module of PFC(Power Factor Correction) that Fairchild has newly developed and designed mainly targeting mid-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to high frequency switching IGBTs. System reliability is further enhanced by the integrated under-voltage lock-out and over-current protection function.

#### Features

- Low thermal resistance due to  $\text{Al}_2\text{O}_3$ -DBC substrate
- 600V-30A 2-phase IGBT PWM semi-converter including a drive IC for gate driving and protection
- Typical switching frequency of 20kHz
- Isolation rating of 2500Vrms/min.

#### Applications

- AC 180V ~ 264V single-phase front-end rectifier

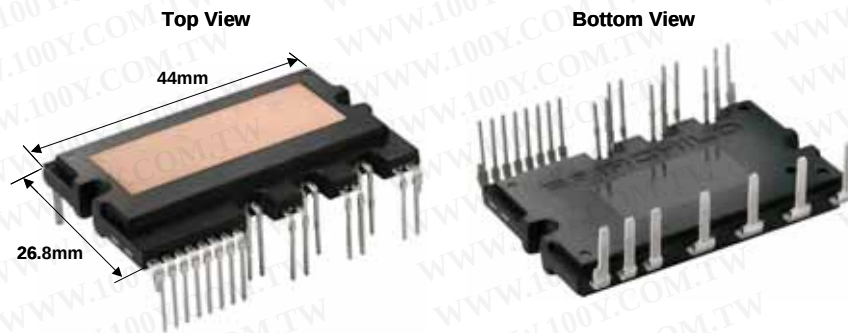


Fig. 1.

## Integrated Power Functions

- PFC converter for single-phase AC/DC power conversion (Please refer to Fig. 3)

## Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Overcurrent circuit protection (OC), Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input

## Pin Configuration

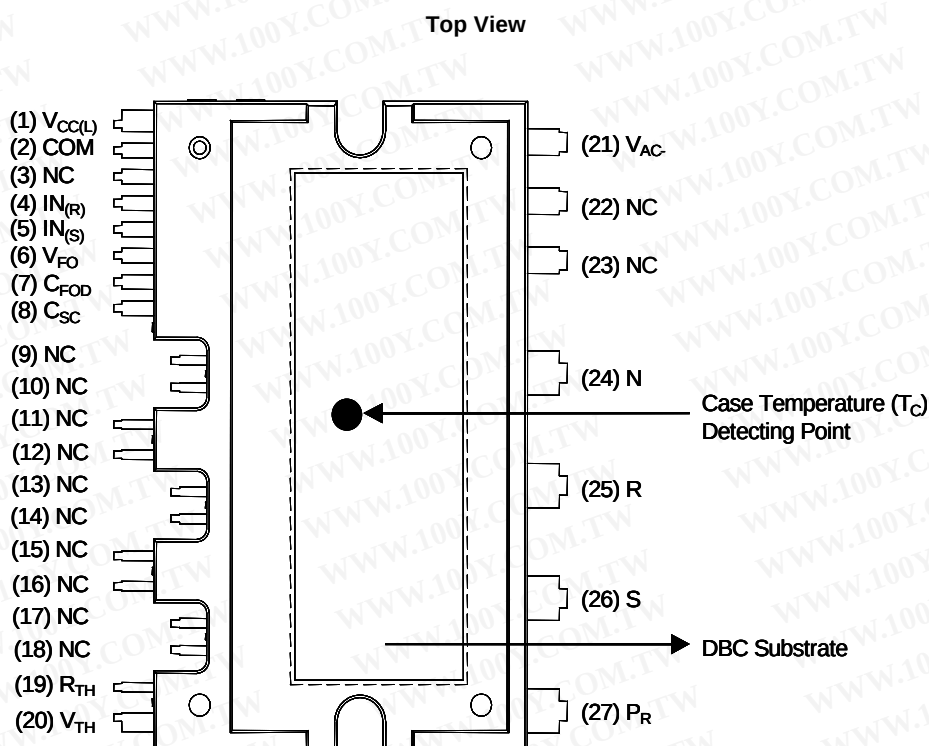
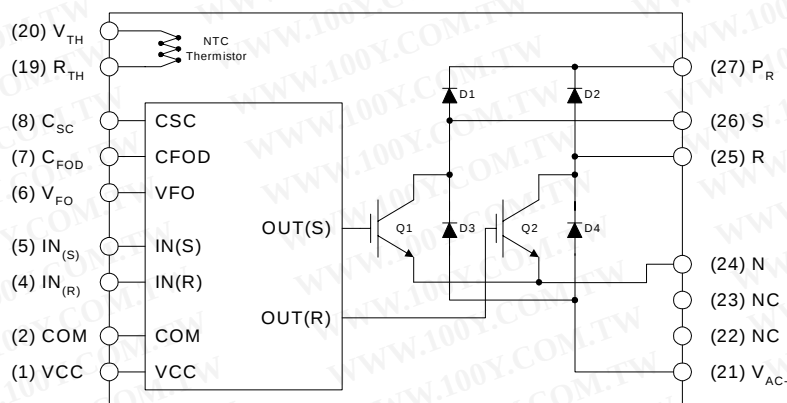


Fig. 2.

## Pin Descriptions

| Pin Number     | Pin Name          | Pin Description                                        |
|----------------|-------------------|--------------------------------------------------------|
| 1              | V <sub>CC</sub>   | Common Bias Voltage for IC and IGBTs Driving           |
| 2              | COM               | Common Supply Ground                                   |
| 4              | IN <sub>(R)</sub> | Signal Input for Low-side R-phase IGBT                 |
| 5              | IN <sub>(S)</sub> | Signal Input for Low-side S-phase IGBT                 |
| 6              | V <sub>FO</sub>   | Fault Output                                           |
| 7              | C <sub>FOD</sub>  | Capacitor for Fault Output Duration Time Selection     |
| 8              | C <sub>SC</sub>   | Capacitor (Low-pass Filter) for Over Current Detection |
| 19             | R <sub>(TH)</sub> | NTC Thermistor terminal                                |
| 20             | V <sub>(TH)</sub> | NTC Thermistor terminal                                |
| 21             | V <sub>AC-</sub>  | Negative Terminal of DC-Link (DIODE) for Sensing       |
| 24             | N                 | Negative Rail of DC-Link (IGBT)                        |
| 25             | R                 | Output for R Phase                                     |
| 26             | S                 | Output for S Phase                                     |
| 27             | P <sub>R</sub>    | Positive Rail of DC-Link                               |
| 3, 9-18, 22-23 | NC                | No Connection                                          |

## Internal Equivalent Circuit and Input/Output Pins



### Note :

1) Converter is composed of two IGBTs including four diodes and one IC which has gate driving and protection functions.

**Fig. 3.**

**Absolute Maximum Ratings** ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)**Converter Part**

| Item                           | Symbol                        | Condition                                                                                                                           | Rating    | Unit             |
|--------------------------------|-------------------------------|-------------------------------------------------------------------------------------------------------------------------------------|-----------|------------------|
| Supply Voltage                 | $V_i$                         | Applied between R-S                                                                                                                 | 264       | $V_{\text{RMS}}$ |
| Supply Voltage (Surge)         | $V_{i(\text{Surge})}$         | Applied between R-S                                                                                                                 | 500       | V                |
| Output Voltage                 | $V_{\text{PN}}$               | Applied between P- N                                                                                                                | 450       | V                |
| Output Voltage (Surge)         | $V_{\text{PN}(\text{Surge})}$ | Applied between P- N                                                                                                                | 500       | V                |
| Collector-emitter Voltage      | $V_{\text{CES}}$              |                                                                                                                                     | 600       | V                |
| Input Current (100% Load)      | $I_i$                         | $T_C < 95^\circ\text{C}$ , $V_i=220\text{V}$ , $V_{\text{PN}}=390\text{V}$ ,<br>$V_{\text{PWM}}=20\text{kHz}$                       | 20        | A                |
| Input Current (125% Load)      | $I_{i(125\%)}$                | $T_C < 95^\circ\text{C}$ , $V_i=220\text{V}$ , $V_{\text{PN}}=390\text{V}$ ,<br>$V_{\text{PWM}}=20\text{kHz}$ , 1min Non-repetitive | 25        | A                |
| Collector Dissipation          | $P_C$                         | $T_C = 25^\circ\text{C}$ per One IGBT                                                                                               | 83        | W                |
| Operating Junction Temperature | $T_J$                         | (Note 1)                                                                                                                            | -20 ~ 125 | $^\circ\text{C}$ |

**Note**

1. The maximum junction temperature rating of the power chips integrated within the SPM is  $150^\circ\text{C}$  ( $@T_C \leq 100^\circ\text{C}$ ). However, to insure safe operation of the SPM, the average junction temperature should be limited to  $T_{J(\text{ave})} \leq 125^\circ\text{C}$  ( $@T_C \leq 100^\circ\text{C}$ )

**Control Part**

| Item                          | Symbol          | Condition                             | Rating                    | Unit |
|-------------------------------|-----------------|---------------------------------------|---------------------------|------|
| Control Supply Voltage        | $V_{\text{CC}}$ | Applied between $V_{\text{CC}}$ - COM | 20                        | V    |
| Input Signal Voltage          | $V_{\text{IN}}$ | Applied between IN - COM              | -0.3~5.5                  | V    |
| Fault Output Supply Voltage   | $V_{\text{FO}}$ | Applied between $V_{\text{FO}}$ - COM | -0.3~ $V_{\text{CC}}+0.3$ | V    |
| Fault Output Current          | $I_{\text{FO}}$ | Sink Current at $V_{\text{FO}}$ Pin   | 5                         | mA   |
| Current Sensing Input Voltage | $V_{\text{SC}}$ | Applied between $C_{\text{SC}}$ - COM | -0.3~ $V_{\text{CC}}+0.3$ | V    |

**Total System**

| Item                              | Symbol           | Condition                                                | Rating    | Unit             |
|-----------------------------------|------------------|----------------------------------------------------------|-----------|------------------|
| Module Case Operation Temperature | $T_C$            |                                                          | -20 ~ 100 | $^\circ\text{C}$ |
| Storage Temperature               | $T_{\text{STG}}$ |                                                          | -40 ~ 125 | $^\circ\text{C}$ |
| Isolation Voltage                 | $V_{\text{ISO}}$ | 60Hz, Sinusoidal, AC 1 minute, Connection<br>Pins to DBC | 2500      | $V_{\text{rms}}$ |

**Thermal Resistance**

| Item                                                              | Symbol              | Condition       | Min. | Typ. | Max. | Unit               |
|-------------------------------------------------------------------|---------------------|-----------------|------|------|------|--------------------|
| Junction to Case Thermal Resistance<br>(Referenced to PKG center) | $R_{\theta(j-c)Q}$  | IGBT            | -    | -    | 1.2  | $^\circ\text{C/W}$ |
|                                                                   | $R_{\theta(j-c)HD}$ | High-side diode | -    | -    | 2.0  | $^\circ\text{C/W}$ |
|                                                                   | $R_{\theta(j-c)LD}$ | Low-side diode  | -    | -    | 1.4  | $^\circ\text{C/W}$ |

**Note :**

2. For the measurement point of case temperature( $T_C$ ), please refer to Fig. 2.

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)**Converter Part**

| Item                                | Symbol        | Condition                                                                                                                                          | Min. | Typ. | Max. | Unit          |
|-------------------------------------|---------------|----------------------------------------------------------------------------------------------------------------------------------------------------|------|------|------|---------------|
| IGBT saturation voltage             | $V_{CE(sat)}$ | $V_{CC} = 15\text{V}$ , $V_{IN} = 5\text{V}$ ; $I_C = 30\text{A}$                                                                                  | -    | 2.4  | 3.1  | V             |
| High-side diode voltage             | $V_{FH}$      | $I_F = 30\text{A}$                                                                                                                                 | -    | 1.9  | 2.5  | V             |
| Low-side diode voltage              | $V_{FL}$      | $I_F = 30\text{A}$                                                                                                                                 | -    | 1.2  | 1.6  | V             |
| Switching Times                     | $t_{ON}$      | $V_{PN} = 400\text{V}$ , $V_{CC} = 15\text{V}$ , $I_C = 30\text{A}$<br>$V_{IN} = 0\text{V} \leftrightarrow 5\text{V}$ , Inductive Load<br>(Note 3) | -    | 550  | -    | ns            |
|                                     | $t_{C(ON)}$   |                                                                                                                                                    | -    | 200  | -    | ns            |
|                                     | $t_{OFF}$     |                                                                                                                                                    | -    | 430  | -    | ns            |
|                                     | $t_{C(OFF)}$  |                                                                                                                                                    | -    | 180  | -    | ns            |
|                                     | $t_{rr}$      |                                                                                                                                                    | -    | 60   | -    | ns            |
|                                     | $I_{rr}$      |                                                                                                                                                    | -    | 6    | -    | A             |
| Collector - emitter Leakage Current | $I_{CES}$     | $V_{CE} = V_{CES}$                                                                                                                                 | -    | -    | 250  | $\mu\text{A}$ |

**Note**

3.  $t_{ON}$  and  $t_{OFF}$  include the propagation delay time of the internal drive IC.  $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Fig. 4

**Control Part**

| Item                                    | Symbol        | Condition                                                            | Min. | Typ. | Max. | Unit       |
|-----------------------------------------|---------------|----------------------------------------------------------------------|------|------|------|------------|
| Quiescent $V_{CC}$ Supply Current       | $I_{QCCL}$    | $V_{CC} = 15\text{V}$ , $I_N = 0\text{V}$ $V_{CC} - \text{COM}$      | -    | -    | 26   | mA         |
| Fault Output Voltage                    | $V_{FOH}$     | $V_{SC} = 0\text{V}$ , $V_{FO}$ Circuit: 4.7k $\Omega$ to 5V Pull-up | 4.5  | -    | -    | V          |
|                                         | $V_{FOL}$     | $V_{SC} = 1\text{V}$ , $V_{FO}$ Circuit: 4.7k $\Omega$ to 5V Pull-up | -    | -    | 0.8  | V          |
| Over Current Trip Level                 | $V_{SC(ref)}$ | $V_{CC} = 15\text{V}$                                                | 0.45 | 0.5  | 0.55 | V          |
| Supply Circuit Under-Voltage Protection | $UV_{CCD}$    | Detection Level                                                      | 10.7 | 11.9 | 13.0 | V          |
|                                         | $UV_{CCR}$    | Reset Level                                                          | 11.2 | 12.4 | 13.2 | V          |
| Fault-out Pulse Width                   | $t_{FOD}$     | $C_{FOD} = 33\text{nF}$ (Note 4)                                     | 1.4  | 1.8  | 2.0  | ms         |
| ON Threshold Voltage                    | $V_{IN(ON)}$  | Applied between IN - COM                                             | 3.0  | -    | -    | V          |
| OFF Threshold Voltage                   | $V_{IN(OFF)}$ |                                                                      | -    | -    | 0.8  | V          |
| Resistance of Thermistor                | $R_{TH}$      | @ $T_C = 25^\circ\text{C}$ (Note Fig. 9)                             | -    | 50   | -    | k $\Omega$ |
|                                         |               | @ $T_C = 80^\circ\text{C}$ (Note Fig. 9)                             | -    | 5.76 | -    | k $\Omega$ |

**Note**

4. The fault-out pulse width  $t_{FOD}$  depends on the capacitance value of  $C_{FOD}$  according to the following approximate equation :  $C_{FOD} = 18.3 \times 10^{-6} \times t_{FOD}[\text{F}]$

Electrical Characteristics

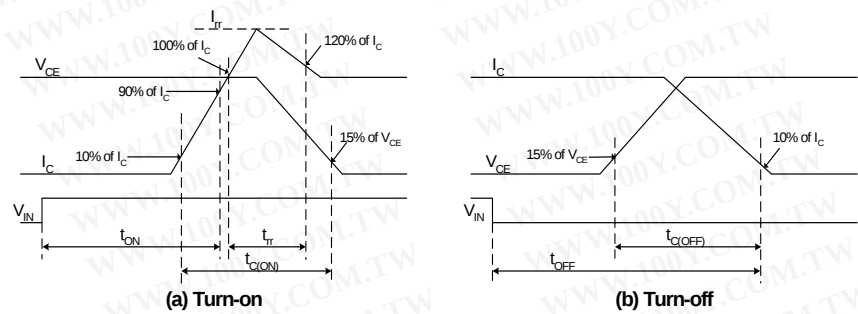


Fig. 4. Switching Time Definition

Mechanical Characteristics and Ratings

| Item            | Condition            |                     | Limits |       |      | Units |
|-----------------|----------------------|---------------------|--------|-------|------|-------|
|                 |                      |                     | Min.   | Typ.  | Max. |       |
| Mounting Torque | Mounting Screw: - M3 | Recommended 0.62N•m | 0.51   | 0.62  | 0.72 | N•m   |
| Device Flatness | Note Fig. 5          |                     | 0      | -     | +120 | μm    |
| Weight          |                      |                     | -      | 15.00 | -    | g     |

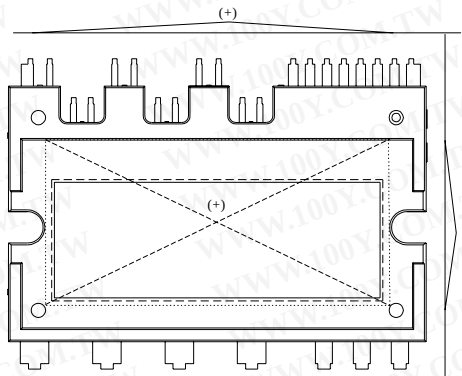
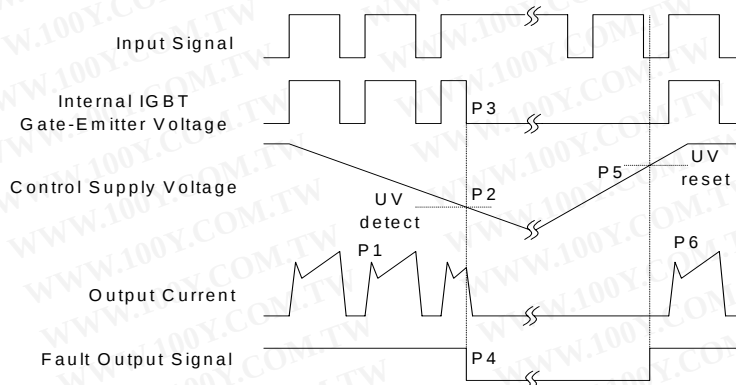


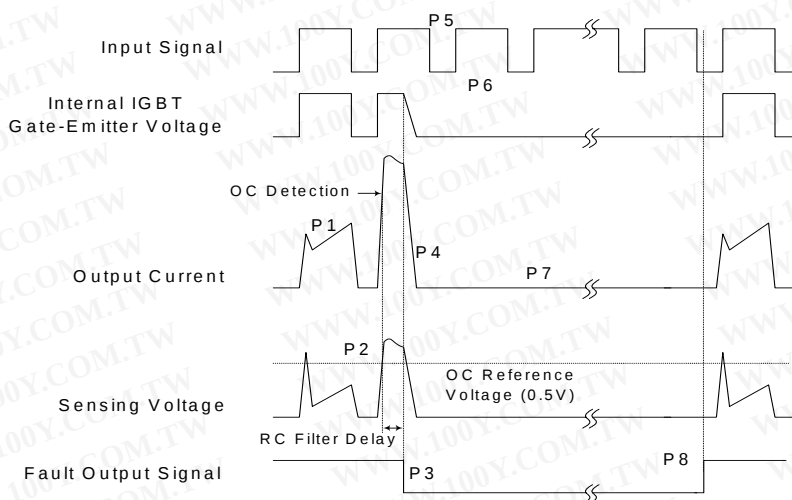
Fig. 5. Flatness Measurement Position

## Time Charts of SPMs Protective Function



- P1 : Normal operation - IGBT ON and conducting current  
 P2 : Under voltage detection  
 P3 : IGBT gate interrupt  
 P4 : Fault signal generation  
 P5 : Under voltage reset  
 P6 : Normal operation - IGBT ON and conducting current

**Fig. 6. Under-Voltage Protection**



- P1 : Normal operation - IGBT ON and conducting current  
 P2 : Over current detection  
 P3 : IGBT gate interrupt / Fault signal generation  
 P4 : IGBT is slowly turned off  
 P5 : IGBT OFF signal  
 P6 : IGBT ON signal - but IGBT cannot be turned on during the fault Output activation  
 P7 : IGBT OFF state  
 P8 : Fault Output reset and normal operation start

**Fig. 7. Over Current Protection**

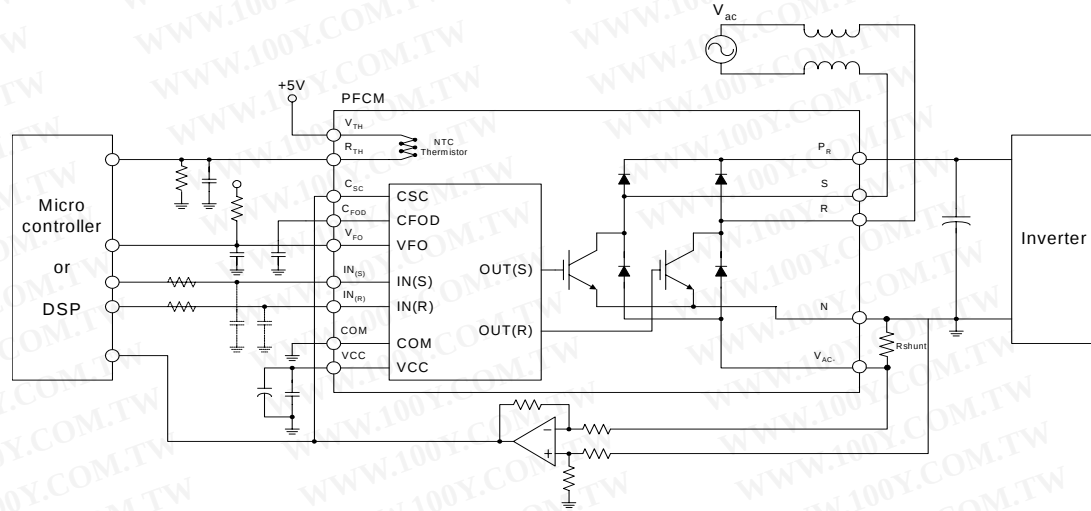


Fig. 8. Application Example

R-T Graph

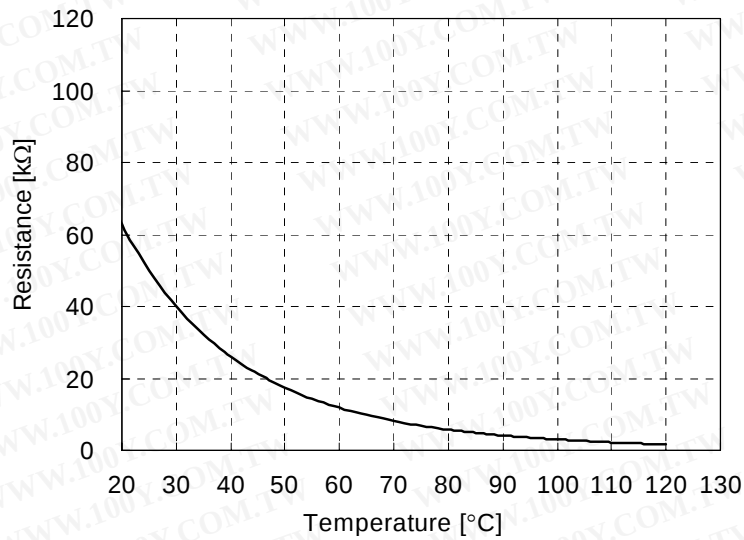
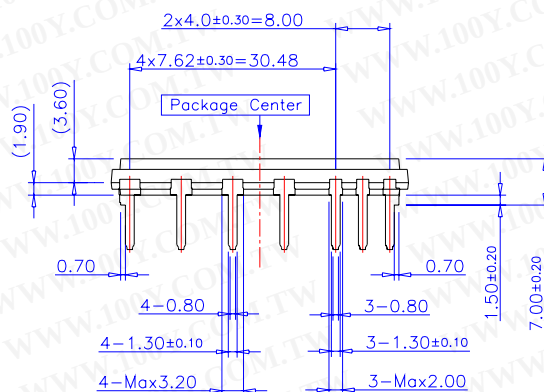
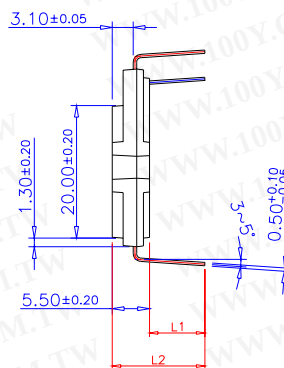
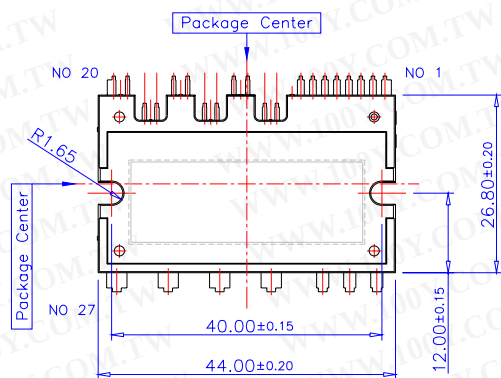
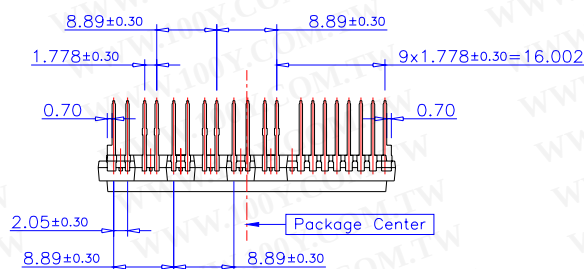


Fig. 9. R-T Curve of the Built-in Thermistor

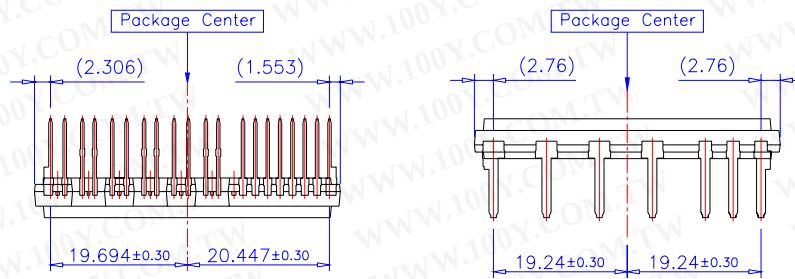
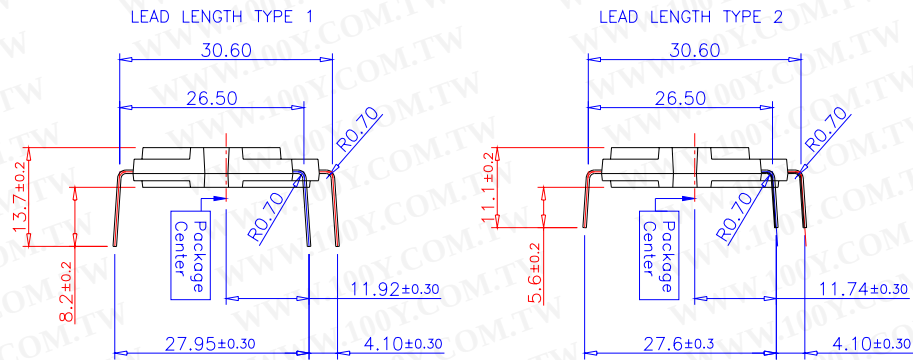
# Detailed Package Outline Drawings



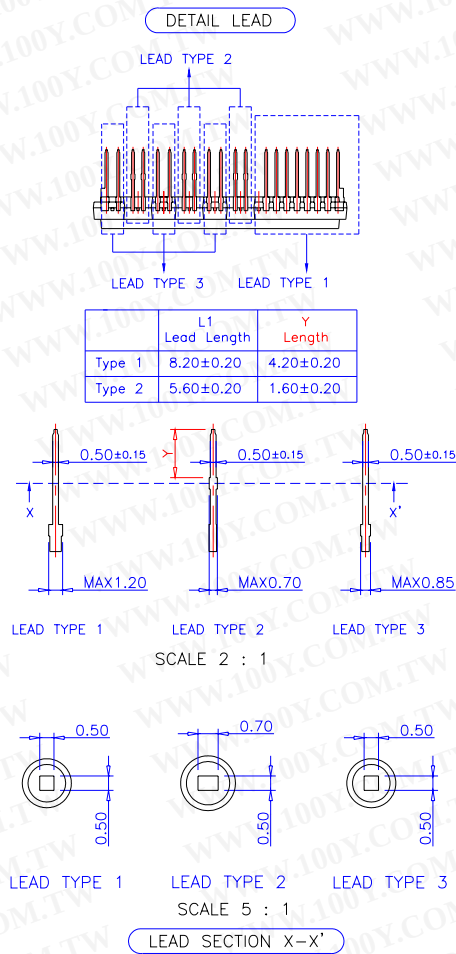
Lead Length Option

|        | L1          | L2         |
|--------|-------------|------------|
|        | Lead Length | PKG Height |
| Type 1 | 8.20±0.20   | 13.7±0.20  |
| Type 2 | 5.60±0.20   | 11.1±0.20  |

# Detailed Package Outline Drawings



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| Build it Now™                        | FRFET™              | MicroFET™     | QS™                 | TCM™            |
| CoolFET™                             | GlobalOptoisolator™ | MicroPak™     | QT Optoelectronics™ | TinyLogic®      |
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| FACT™                                | IntelliMAX™         | OPTOLOGIC®    | SILENT SWITCHER®    | VCX™            |
| FACT Quiet Series™                   |                     | OPTOPLANAR™   | SMART START™        | Wire™           |
| Across the board. Around the world.™ |                     | PACMAN™       | SPM™                |                 |
| The Power Franchise®                 |                     | POP™          | Stealth™            |                 |
| Programmable Active Droop™           |                     | Power247™     | SuperFET™           |                 |
|                                      |                     | PowerEdge™    | SuperSOT™-3         |                 |

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